

Patent Abstracts of Japan

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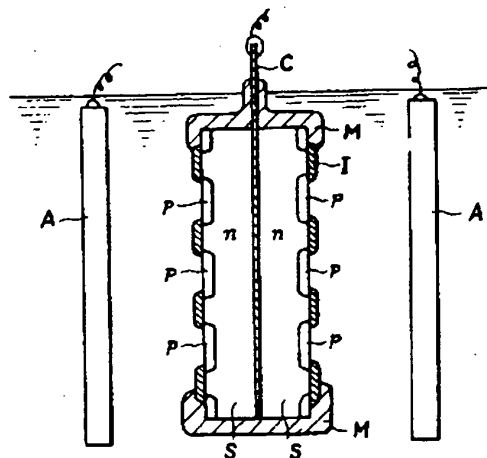
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TITLE : ELECTROLYTE PLATING METHOD
FOR SEMICONDUCTOR WAFER



ABSTRACT : PURPOSE: To prevent contact between wafer and electrolyte and to supply a voltage to a metal plate by closely placing in contact the rear surfaces of two sheets of semiconductor wafers holding said metal plate between them.

CONSTITUTION: The rear surfaces of two sheets of n type silicon wafers S are closely placed in contact each other through a metal place C and thereby protected from contact with the electrolyte. In order to protect the side surfaces of silicon wafers S from electrolyte, a small amount of film M is attached. A voltage is supplied to a metal plate C. Thereby, the n type region of silicon wafer S, p-n junction just below the surface, p type region at the surface and a current path which reaches the electrode A through electrolyte are respectively formed and the electrolyte plated layer is further formed in the p type region at the surface. As a metal plate C, a soft metal having high expandability such as indium and gold is just suitable in order to obtain excellent electrical contact with the silicon wafer S.

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